

	Document ID	Issue Date	Current OR	Inventor
1	US 6297162 B1	20011002	438/706	Jang, Syun-Ming et al.
2	US 6265321 B1	20010724	438/725	Chooi, Simon et al.
3	US 6083822 A	20000704	438/624	Lee, Tze-Liang

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	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	116	dual near damascene and etch near stop near layer and (hardmask or mask) and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4)	USPAT	2002/12/0 1 22:12
2	BRS	2	dual near damascene and etch near stop near layer and (hardmask or mask) and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4) and ("oxygen-doped silicon carbide" or "SiCO")	USPAT	2002/12/0 1 22:10
3	BRS	16	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and (("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4)) with barrier near layer	USPAT	2002/12/0 1 22:32
4	BRS	16	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and (("SiO" or silicon near (oxide or dioxide)) same ("SiN" or silicon near nitr\$4)) same passivation near layers	USPAT	2002/12/0 1 22:44

	Type	Hits	Search Text	DBs	Time Stamp
5	BRS	1	"5324683".PN.	USPAT	2002/12/01 22:43
6	BRS	1	"5407860".PN.	USPAT	2002/12/01 22:43
7	BRS	1	"5461003".PN.	USPAT	2002/12/01 22:43
8	BRS	1	"5510645".PN.	USPAT	2002/12/01 22:43
9	BRS	1	"5750415".PN.	USPAT	2002/12/01 22:43
10	BRS	1	"5950102".PN.	USPAT	2002/12/01 22:44
11	BRS	35	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4) and passivation near layers	USPAT	2002/12/01 23:13
12	BRS	143	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4)	USPAT	2002/12/01 23:07
13	BRS	3	"6297162"	USPAT	2002/12/01 23:07
14	BRS	1	"5188704".PN.	USPAT	2002/12/01 23:07
15	BRS	1	"5198392".PN.	USPAT	2002/12/01 23:07
16	BRS	1	"5536681".PN.	USPAT	2002/12/01 23:08
17	BRS	1	"5766974".PN.	USPAT	2002/12/01 23:08
18	BRS	1	"5930627".PN.	USPAT	2002/12/01 23:08
19	BRS	1	"6004873".PN.	USPAT	2002/12/01 23:08

	Type	Hits	Search Text	DBs	Time Stamp
20	BRS	1	"6069077".PN.	USPAT	2002/12/01 23:09
21	BRS	1	"6140266".PN.	USPAT	2002/12/01 23:09
22	BRS	2	(6265321.pn. or 6297162.pn. or 6083822.pn.) and dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4) and passivation near layers	USPAT	2002/12/01 23:33
23	BRS	0	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4) and passivation near layers with ("nitrogen" near ("silicon carbide" or "SiC") and "oxygen" near ("silicon carbide" or "SiC"))	USPAT	2002/12/02 00:15
24	BRS	2411	silicates with ("silicon carbide" or "SiC")	USPAT	2002/12/01 23:45
25	BRS	1227	dielectric near constant with silicon near dioxide	USPAT	2002/12/02 00:02
26	BRS	570	257/\$.ccls. and dielectric near constant with silicon near dioxide	USPAT	2002/12/02 00:13

	Type	Hits	Search Text	DBs	Time Stamp
27	BRS	5644	257/\$.ccls. and (silicates with doped (carbon) or silicon near oxide with carbon)	USPAT	2002/12/0 2 00:14
28	BRS	0	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4) and passivation near layers with (("nitrogen" near ("silicon carbide" or "SiC") or "oxygen" near ("silicon carbide" or "SiC")))	USPAT	2002/12/0 2 01:25
29	BRS	6	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4) and passivation near layers with("silicon carbide" or "SiC")	USPAT	2002/12/0 2 00:20
30	BRS	10	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) with carbon and ("SiN" or silicon near nitr\$4) with carbon	USPAT	2002/12/0 2 00:21

	Type	Hits	Search Text	DBs	Time Stamp
31	BRS	35	dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer and ("SiO" or silicon near (oxide or dioxide)) and ("SiN" or silicon near nitr\$4) and passivation near layers	USPAT	2002/12/02 01:28
32	BRS	43	(257/750 or 257/751 or 257/752 or 257/753 or 257/754) and dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 01:33
33	BRS	37	(257/755 or 257/756 or 257/757 or 257/758 or 257/759) and dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 01:37
34	BRS	32	(257/760 or 257/762) and dual near damascene and etch near stop near layer and copper with (conductive or metal or wiring) near layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 01:38
35	BRS	0	dual near damascene and etch near stop near layer and (conductive or metal or wiring) near layer	JPO	2002/12/02 01:39
36	BRS	1	dual near damascene and etch near stop near layer	JPO	2002/12/02 01:41

	Type	Hits	Search Text	DBs	Time Stamp
37	BRS	0	6297162.pn. or 6083822.pn. or 6265321.pn.	JPO	2002/12/0 2 01:42
38	BRS	3	6297162.pn. or 6083822.pn. or 6265321.pn.	USPAT	2002/12/0 2 01:42